

ABSTRACT OF THE DISCLOSURE

A method of manufacturing a semiconductor substrate (7) includes the processes of: forming an insulation film (2) on a surface of a semiconductor substrate main body (1); forming an ion shield member (3) having a predetermined shape on the insulation film; implanting an ion into the semiconductor substrate main body from a side on which the insulation film is formed, to thereby form an ion implantation layer (1a, 1b); removing the ion shield member; laminating the insulation film and a support substrate (5) onto each other; and separating the semiconductor substrate main body from the support substrate at a portion of the ion implantation layer.